# ne<mark>x</mark>peria

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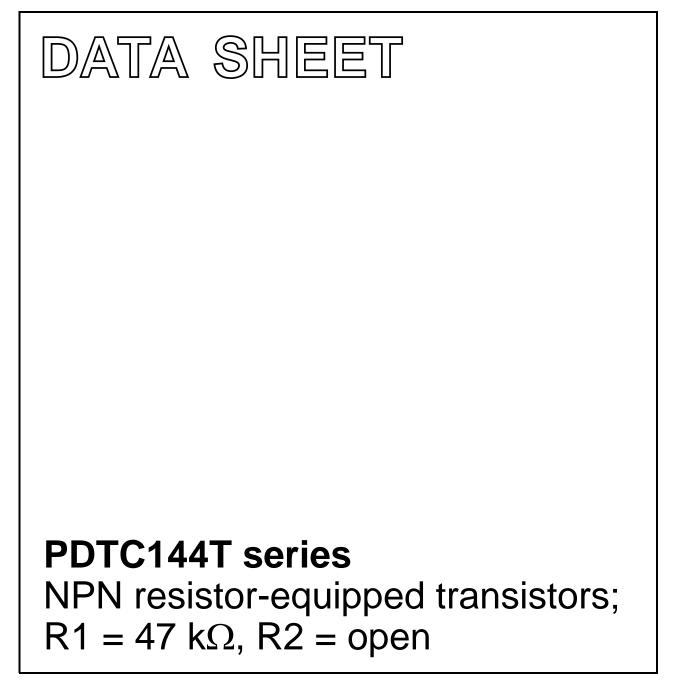
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2004 Apr 06 2004 Aug 17



### **PDTC144T series**

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### **PRODUCT OVERVIEW**

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	_	50	V
lo	output current (DC)	-	100	mA
R1	bias resistor	47	-	kΩ
R2	open	_	-	-

### DESCRIPTION

NPN resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT	
ITPE NUMBER	PHILIPS	EIAJ	MARKING CODE		
PDTC144TE	SOT416	SC-75	43	PDTA144TE	
PDTC144TEF	SOT490	SC-89	33	PDTA144TEF	
PDTC144TK	SOT346	SC-59	53	PDTA144TK	
PDTC144TM	SOT883	SC-101	E4	PDTA144TM	
PDTC144TS	SOT54 (TO-92)	SC-43	TC144T	PDTA144TS	
PDTC144TT	SOT23	_	*41 <sup>(1)</sup>	PDTA144TT	
PDTC144TU	SOT323	SC-70	*41 <sup>(1)</sup>	PDTA144TU	

### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

# NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$ , R2 = open

# PDTC144T series

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

	R SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
TYPE NUMBER			DESCRIPTION		
PDTC144TS	$\begin{bmatrix} 1 \\ 2 \\ 3 \end{bmatrix}$ $\begin{bmatrix} R_1 \\ R_1 $	PIN 1 2 3	DESCRIPTION base collector emitter		
PDTC144TE PDTC144TEF PDTC144TK PDTC144TT PDTC144TU	3     1     3       1     2       Top view     MDB270	1 2 3	base emitter collector		
PDTC144TM	2 1 Bottom view MHC507	1 2 3	base emitter collector		

# NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$ , R2 = open

# PDTC144T series

### **ORDERING INFORMATION**

	PACKAGE			
TYPE NUMBER	NAME	DESCRIPTION	VERSION	
PDTC144TE	_	<ul> <li>plastic surface mounted package; 3 leads</li> </ul>		
PDTC144TEF	_	plastic surface mounted package; 3 leads SOT		
PDTC144TK	_	plastic surface mounted package; 3 leads SOT3		
PDTC144TM	_	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm		
PDTC144TS	_	<ul> <li>plastic single-ended leaded (through hole) package; 3 leads</li> <li>SC</li> </ul>		
PDTC144TT	<ul> <li>plastic surface mounted package; 3 leads</li> <li>SC</li> </ul>		SOT23	
PDTC144TU	_	plastic surface mounted package; 3 leads SOT32		

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
lo	output current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
	SOT416	note 1	-	150	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

## PDTC144T series

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W
	SOT416	note 1	833	K/W

### Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

### CHARACTERISTICS

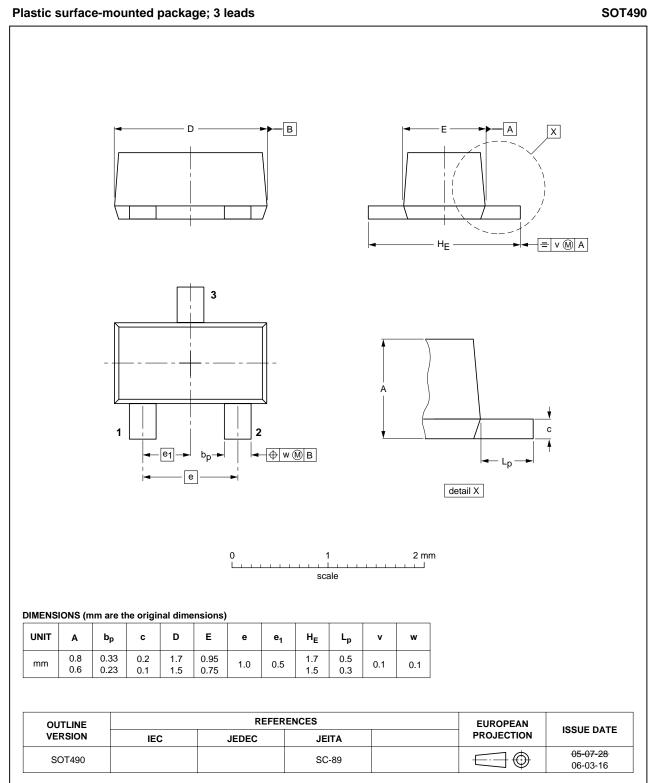
 $T_{amb}$  = 25 °C unless otherwise specified.

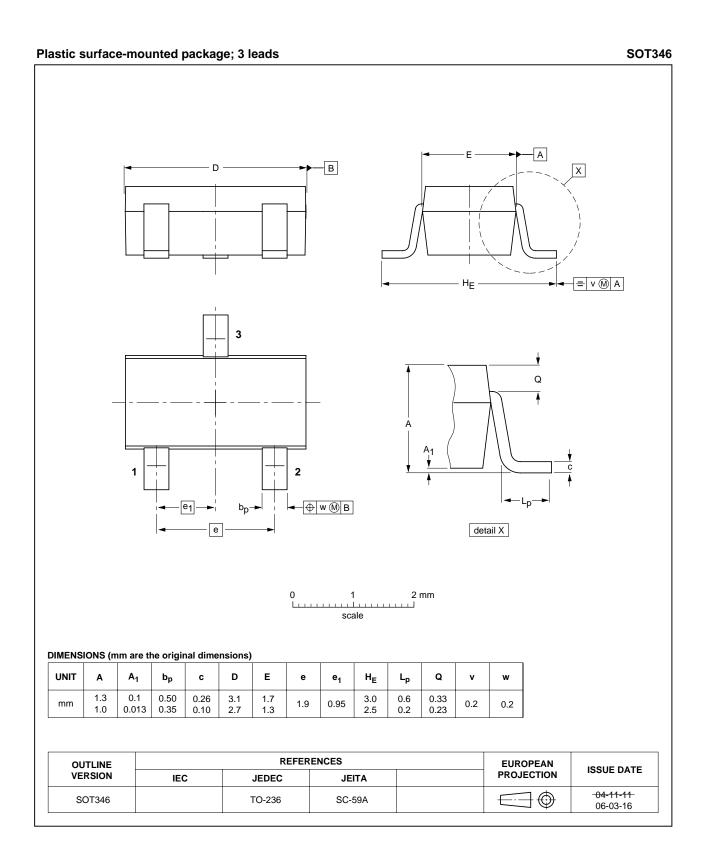
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A	_	-	1	μA
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V; I_C = 0 A$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 mA	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	-	-	150	mV
R1	input resistor		33	47	61	kΩ
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	-	-	2.5	pF

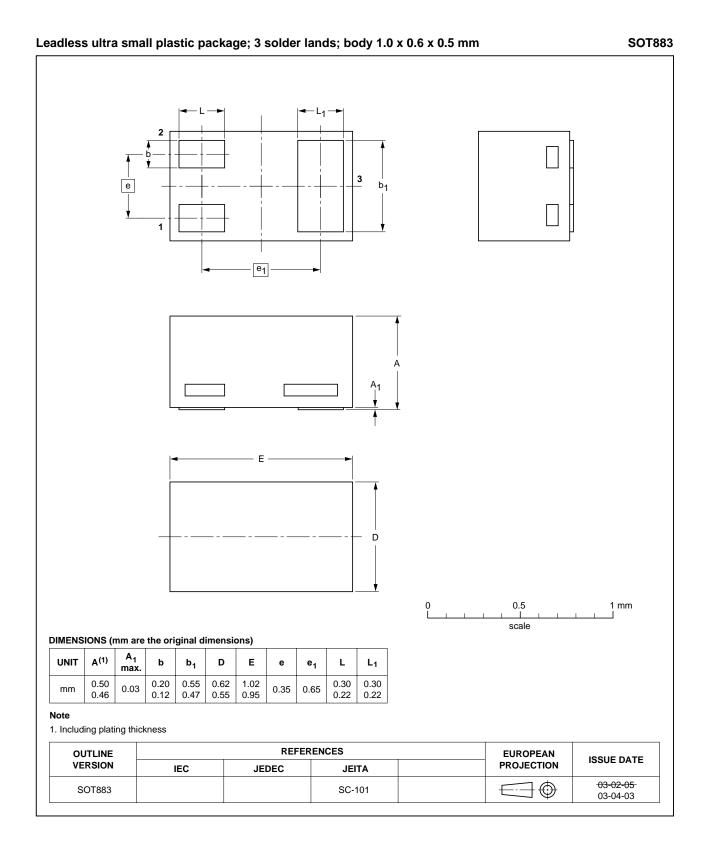
PDTC144T series

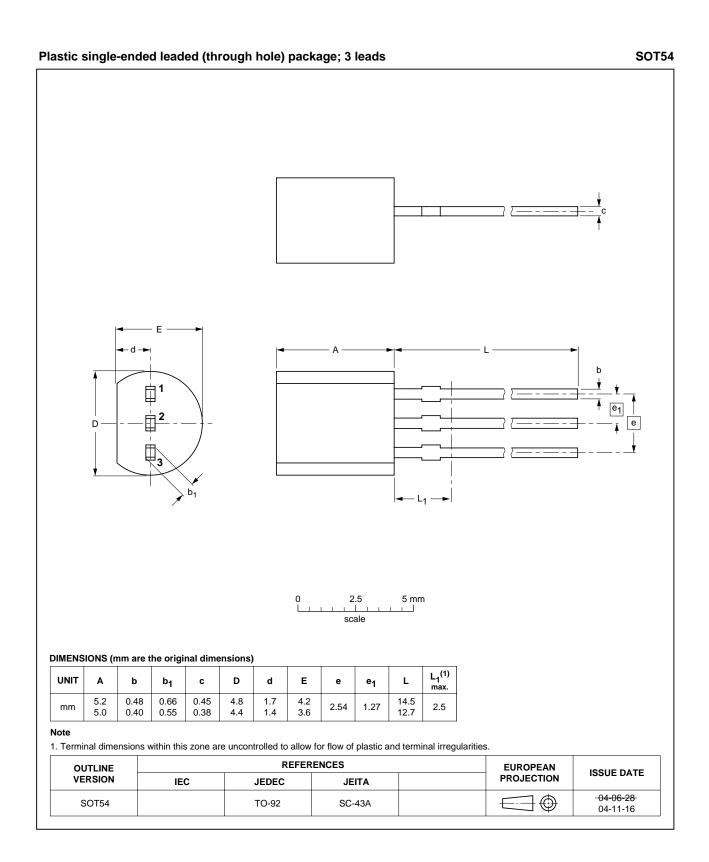
# NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$ , R2 = open

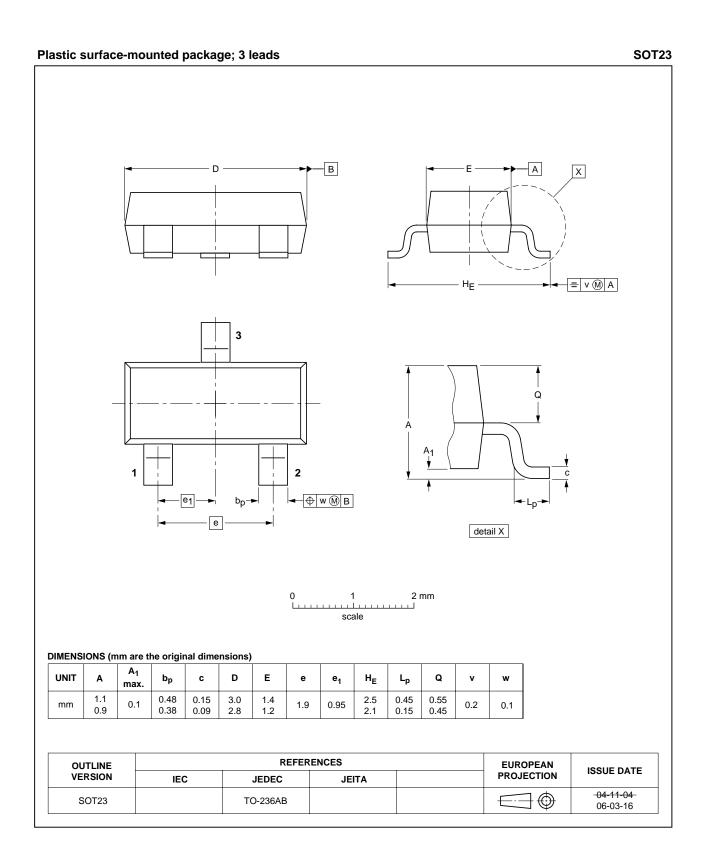
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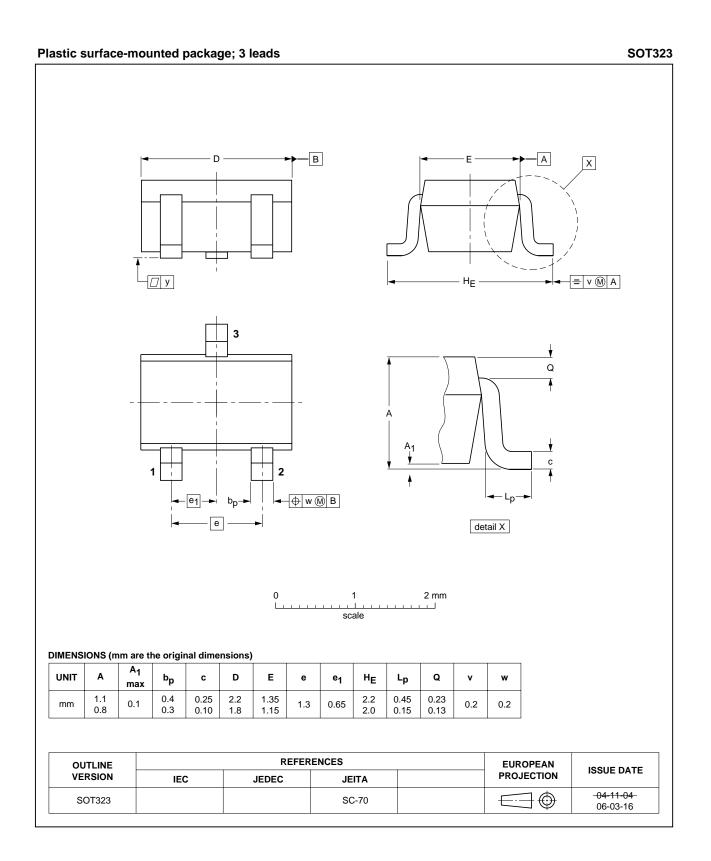


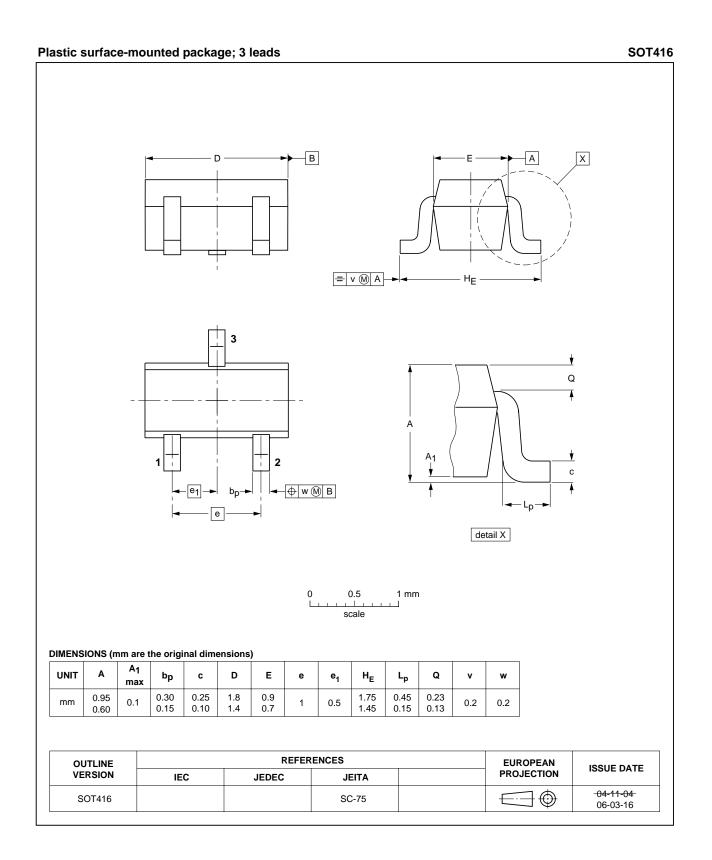












## PDTC144T series

### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# **NXP Semiconductors**

### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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